



100-8 1A Sensitive SCR

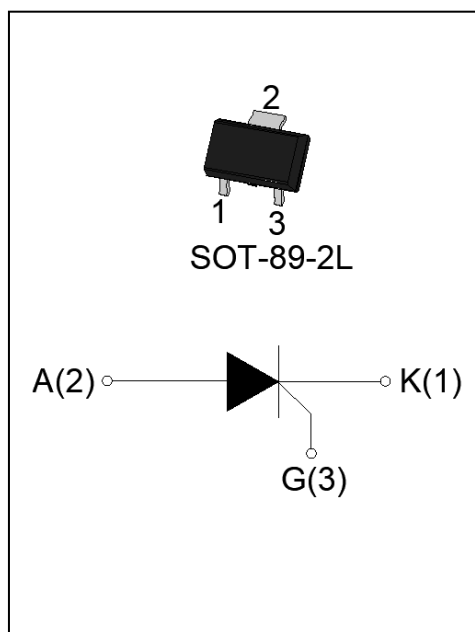
Rev.A.1.0

DESCRIPTION:

The 100-8 SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package SOT-89-2L is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM} / V_{RRM}	800	V
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125 ^①	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 72^{\circ}C$)	$I_{T(AV)}$	0.6	A
RMS on-state current ($T_c \leq 72^{\circ}C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^{\circ}C$)	I_{TSM}	12	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^{\circ}C$)		13	
I^2t value for fusing ($t_p=10ms, T_j=25^{\circ}C$)	I^2t	0.72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^{\circ}C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^{\circ}C$)	I_{GM}	1	A
Average gate power dissipation ($T_j=125^{\circ}C$)	$P_{G(AV)}$	0.1	W

Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	1	kV

NOTE 1: When we parallel connect a $\leq 1\text{K}\Omega$ resistor between Gate and Cathode, the T_j can reach 125°C ; if without this resistor, the T_j only can reach 110°C .

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	40	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	5	mA
I_H	$I_T=0.05\text{A}$	-	-	4	mA
dV/dt	$V_D=540\text{V } T_j=125^\circ\text{C } R_{GK}=1\text{K}\Omega$	200	-	-	V/ μs
	$V_D=540\text{V } T_j=125^\circ\text{C } R_{GK}=220\Omega$	500	-	-	
t_{on}	$I_G=10\text{mA } I_A=20\text{mA } I_R=2\text{mA}$	-	2	-	μs
t_{off}	$T_j=25^\circ\text{C}$	-	50	-	μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_T=2\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.8	V
R_D	Dynamic Resistance	$T_j=125^\circ\text{C}$	0.1	Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	45	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (DC, in free air, $S=5\text{cm}^2$)	100	$^\circ\text{C}/\text{W}$

MARKING

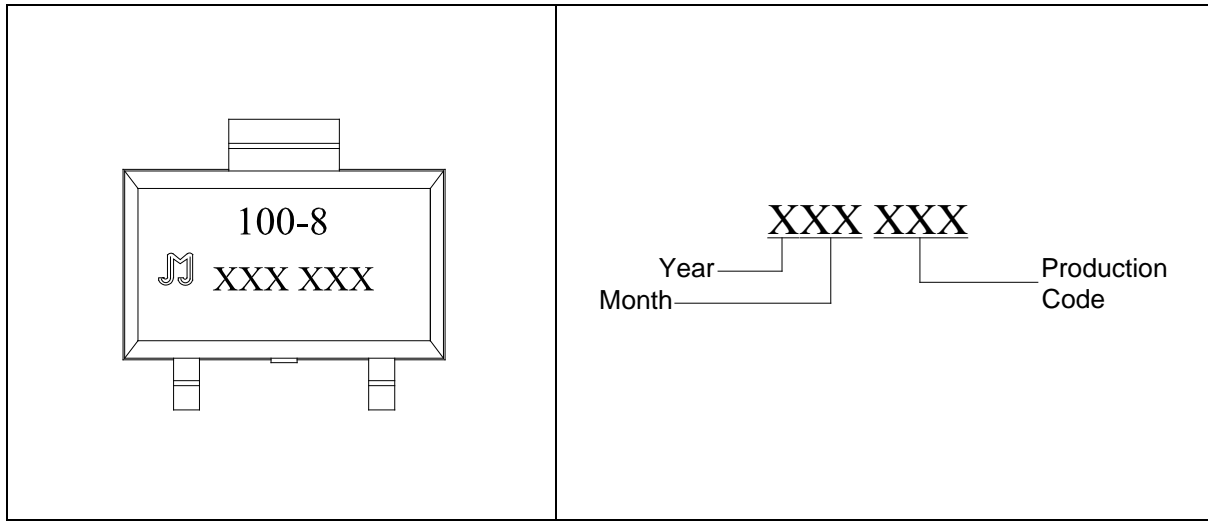


FIG.1 Maximum power dissipation versus RMS on-state current

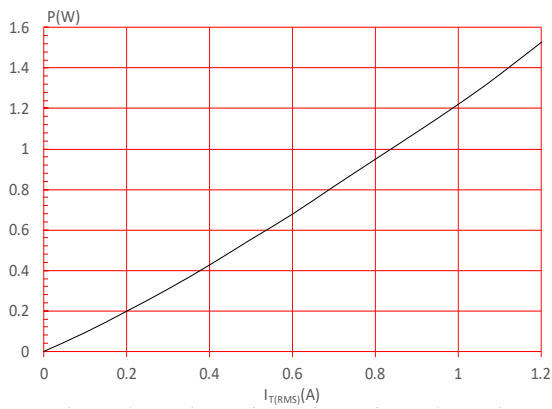


FIG.2: RMS on-state current versus case temperature

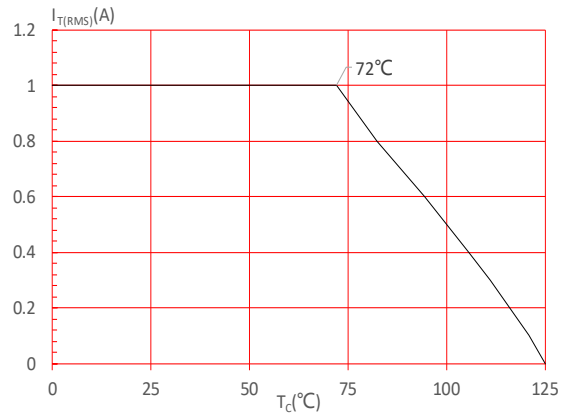


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

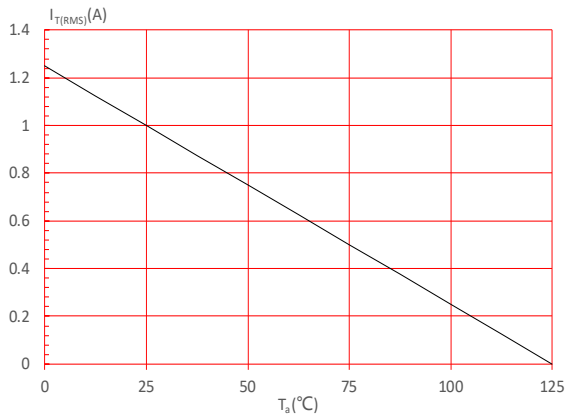


FIG.4: Surge peak on-state current versus number of cycles

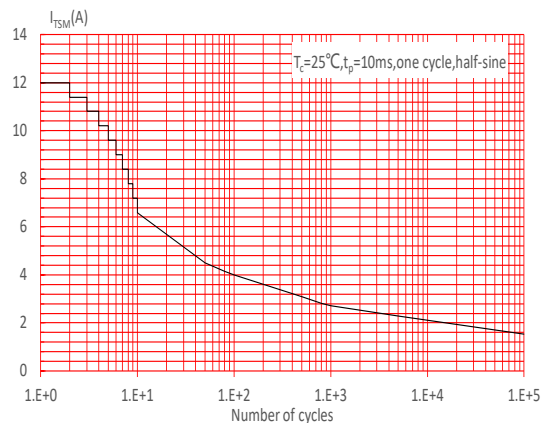


FIG.5: On-state characteristics

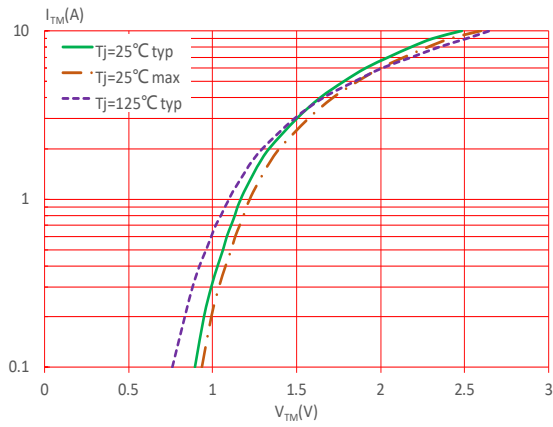


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

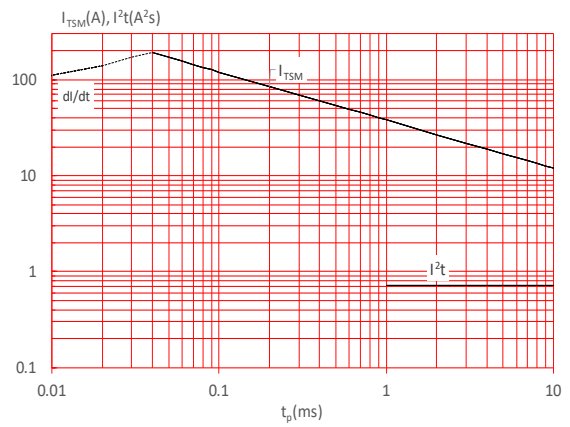


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

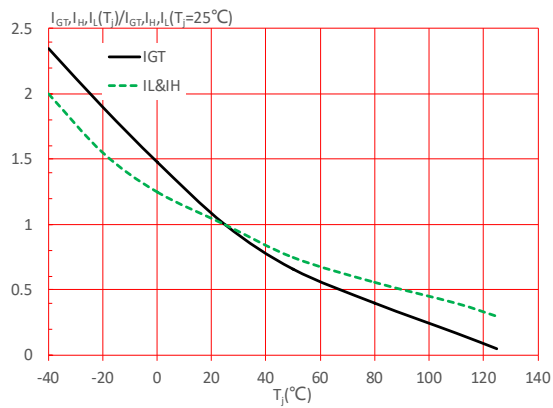
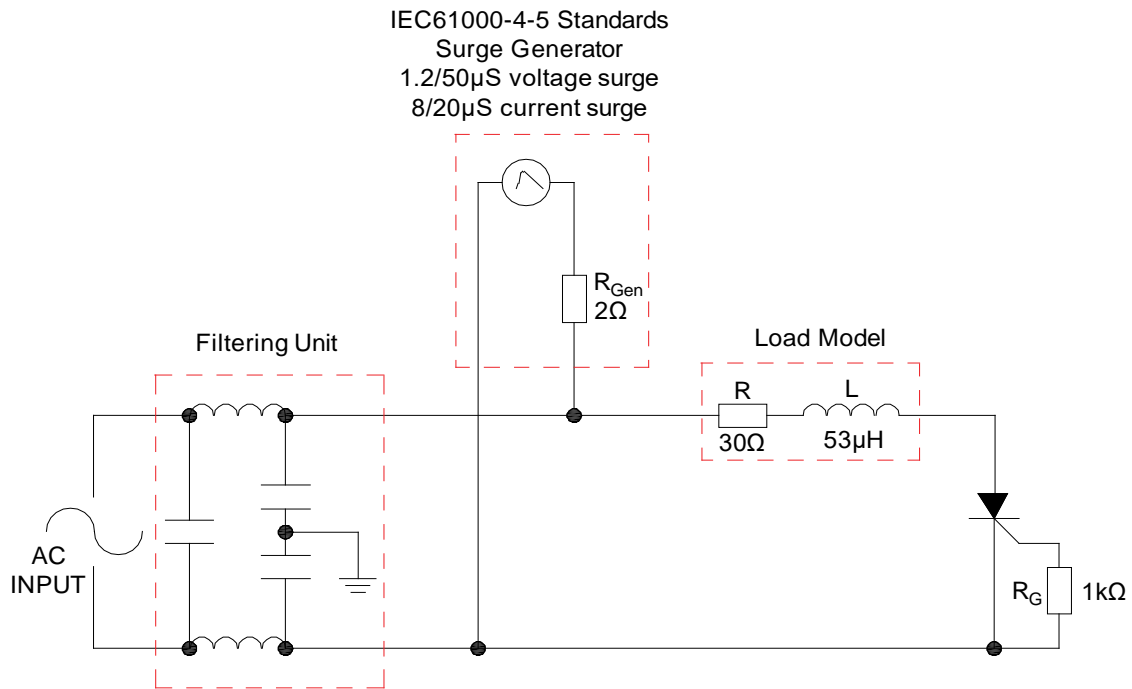
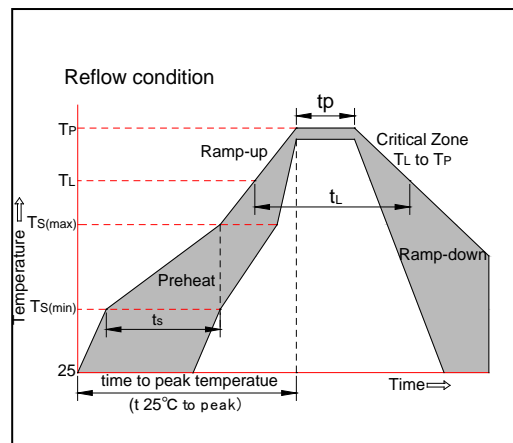


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{S(min)}$)	+150°C
	-Temperature Max ($T_{S(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{S(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



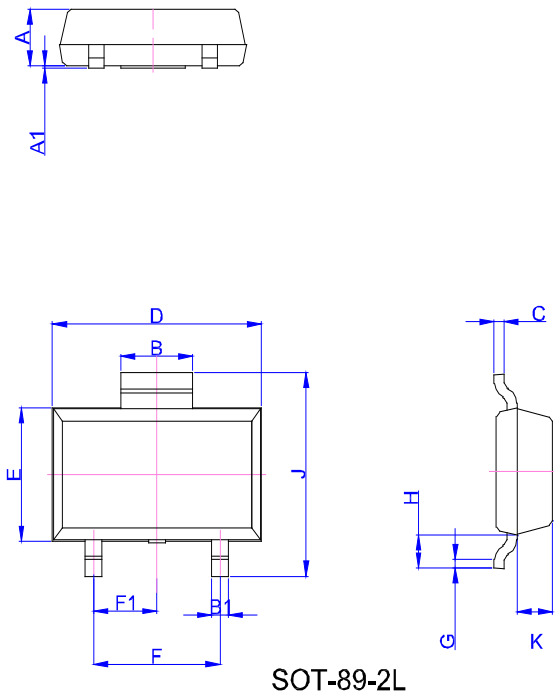
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(μ A)	Package	Base qty. (pcs)	Delivery mode
100-8	800	≤ 200	SOT-89-2L	4,000	Tape & Reel

Document Revision History

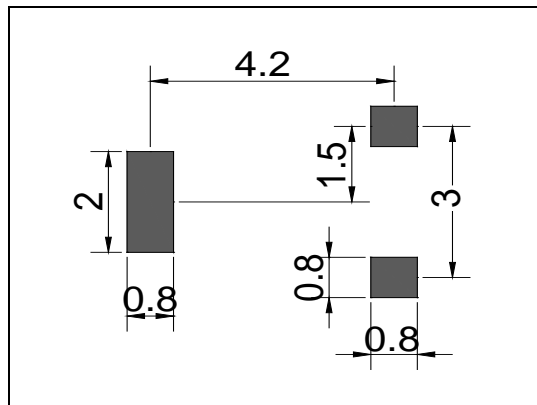
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA

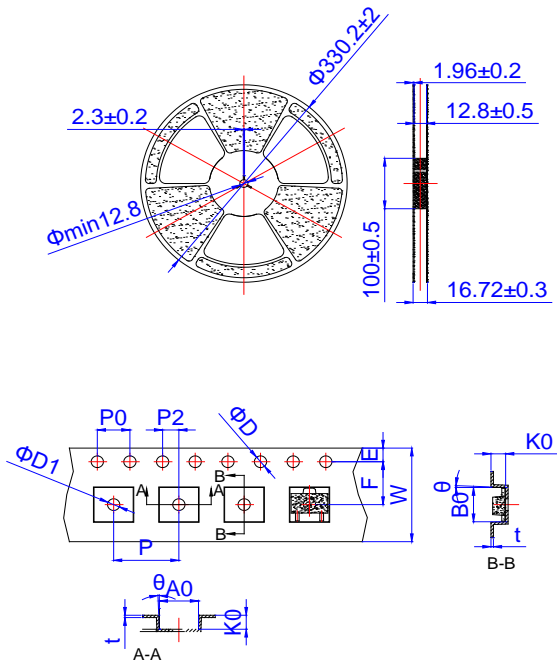


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.3	1.4	1.5	0.051	0.055	0.059
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	1.6	1.7	1.8	0.063	0.067	0.071
B1	0.3	0.4	0.5	0.012	0.016	0.020
C	0.22	0.254	0.32	0.009	0.010	0.013
D	4.75	4.95	5.15	0.187	0.195	0.203
E	2.90		3.30	0.114		0.130
F	2.80		3.20	0.110		0.126
F1	1.40		1.60	0.055		0.063
G	0.20	0.30	0.40	0.008	0.012	0.016
H	0.58	0.78	0.98	0.023	0.031	0.039
J	4.30	4.50	4.70	0.169	0.177	0.185
K	0.80		1.00	0.031		0.039

FOOTPRINT-SOT-89-2L (dimensions in mm)




DELIVERY MODE



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50	-	-	0.059	-	-
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W	-	-	12.30	-	-	0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95	0.069	0.073	0.076
t	0.20	0.25	0.30	0.008	0.010	0.012
θ	3°		5°	3°		5°

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
SOT-89-2L	TAPING	4,000	40,000	13 inch

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